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**CMPD5001
CMPD5001S**

**HIGH CURRENT
INDUCTIVE LOAD
SWITCHING DIODE**



SOT-23 CASE

The following configurations are available:

**CMPD5001 SINGLE
CMPD5001S DUAL, IN SERIES**

捷多邦，专业PCB打样工厂，24小时加急出货™
**Central
Semiconductor Corp.**

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPD5001 series types are silicon switching diodes manufactured by the epitaxial planar process, designed for switching inductive load applications requiring extremely high current capability.

MAXIMUM RATINGS (T_A=25°C)

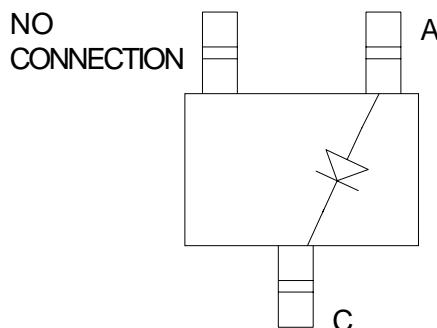
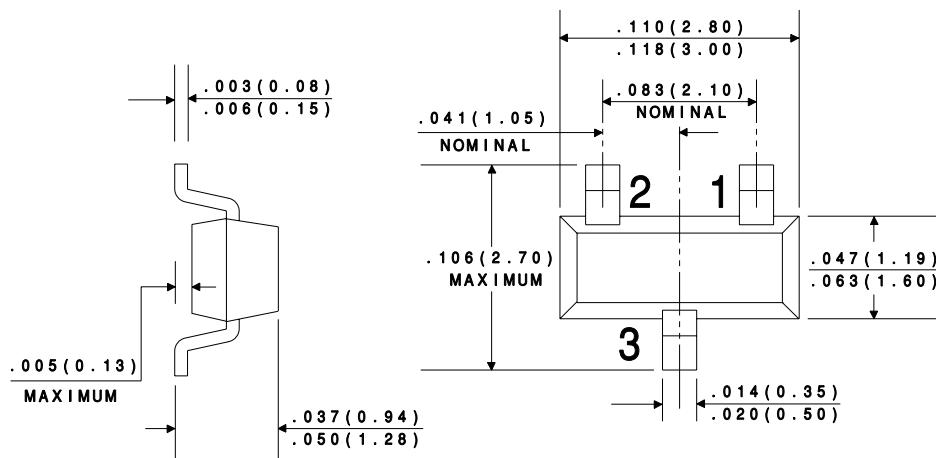
	SYMBOL		UNITS
Continuous Reverse Voltage	V _R	120	V
Continuous Forward Current	I _F	400	mA
Peak Repetitive Forward Current	I _{FRM}	800	mA
Peak Repetitive Reverse Current	I _{RRM}	600	mA
Forward Surge Current, t _p =1 μs	I _{FSM}	6000	mA
Forward Surge Current, t _p =1 s	I _{FSM}	1500	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

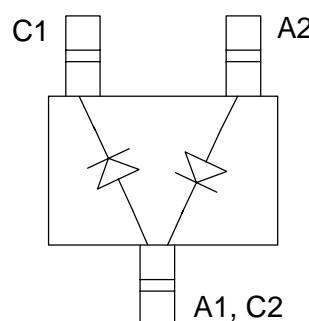
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
B _{VR}	I _R =1.0mA	120	175	V
I _R	V _R =90V		100	nA
I _R	V _R =90V, T _A =150°C		100	μA
V _F	I _F =10mA		0.75	V
V _F	I _F =50mA		0.84	V
V _F	I _F =100mA		0.90	V
V _F	I _F =200mA		1.00	V

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V_F	$I_F=400\text{mA}$		1.25	V
C_T	$V_R=0, f=1 \text{ MHz}$		35	pF
t_{rr}	$I_F=I_R=30\text{mA}, \text{RECOV. TO } 1.0\text{mA}, R_L=100\Omega$		60	ns
t_{rr}	$I_F=I_R=10\text{mA}, \text{RECOV. TO } 1.0\text{mA}, R_L=100\Omega$		50	ns

All dimensions in inches (mm).



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